

NJ1800DL Process

Silicon Junction Field-Effect Transistor

- Low-Current
- Low Gate Leakage Current
- High Input Impedance
- Low-Noise

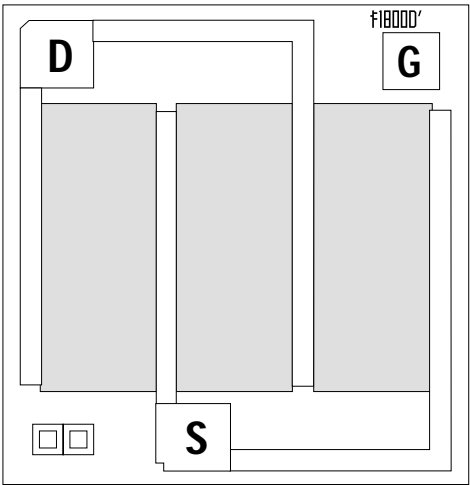
Absolute maximum ratings at 25 °C free-air temperature.

Gate Current, I _g	10 mA
Operating Junction Temperature, T _j	+150°C
Storage Temperature, T _s	– 65°C to +175°C

Device in this Databook based on the NJ1800DL Process.

Datasheet

IF1801



Die Size = 0.052" X 0.052"
All Bond Pads ≥ 0.004" Sq.
Substrate is also Gate.

www.DataSheet4U.com

At 25°C free air temperature:

Static Electrical Characteristics

		NJ1800DL Process					
		Min	Typ	Max	Unit	Test Conditions	
Gate Source Breakdown Voltage	V _{(BR)GSS}	– 15	– 25		V	I _G = – 1 μA, V _{DS} = 0V	
Reverse Gate Leakage Current	I _{GSS}		– 30	– 100	pA	V _{GS} = – 10V, V _{DS} = 0V	
Drain Saturation Current (Pulsed)	I _{DSS}	50		800	mA	V _{DS} = 10V, V _{GS} = 0V	
Gate Source Cutoff Voltage	V _{GS(OFF)}	– 0.1		– 4	V	V _{DS} = 10V, I _D = 1 nA	

Dynamic Electrical Characteristics

Forward Transconductance (Pulsed)	g _{fs}		350		mS	V _{DS} = 10V, V _{GS} = 0V	f = 1 kHz
Input Capacitance	C _{iss}		160		pF	I _D = 1 mA, V _{GS} = 0V	f = 1 MHz
Feedback Capacitance	C _{rss}		50		pF	V _{DS} = 10V, V _{GS} = 0V	f = 1 MHz
Equivalent Noise Voltage	e _N		0.7		nV/√HZ	V _{DG} = 4V, I _D = 5 mA	f = 1 kHz

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